PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1 Stylesheet Version v1.2 EPAS ID: PAT3989995

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT

CONVEYING PARTY DATA

Name	Execution Date
SANDISK CORPORATION	07/12/2016

RECEIVING PARTY DATA

Name:	SANDISK TECHNOLOGIES LLC
Street Address:	6900 DALLAS PARKWAY
Internal Address:	SUITE 325
City:	PLANO
State/Country:	TEXAS
Postal Code:	75024

PROPERTY NUMBERS Total: 49

Property Type	Number
Application Number:	09893277
Application Number:	10323534
Application Number:	10966451
Application Number:	11205595
Application Number:	10353574
Application Number:	11004139
Application Number:	11003046
Application Number:	11419696
Application Number:	10051372
Application Number:	10656139
Application Number:	11049535
Application Number:	11417185
Application Number:	11871441
Application Number:	12168283
Application Number:	12652418
Application Number:	12967227
Application Number:	13482577
Application Number:	14078195
Application Number:	14559265

PATENT REEL: 039551 FRAME: 0231

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Property Type	Number
Application Number:	14983802
Application Number:	10665685
Application Number:	11389557
Application Number:	10823737
Application Number:	11289509
Application Number:	11391299
Application Number:	11387818
Application Number:	12108272
Application Number:	12846118
Application Number:	13099024
Application Number:	10689333
Application Number:	11624052
Application Number:	60612089
Application Number:	11319895
Application Number:	61822009
Application Number:	14018790
Application Number:	14200819
Application Number:	14638817
Application Number:	61876539
Application Number:	14199082
Application Number:	60356455
Application Number:	09838817
Application Number:	12038666
Application Number:	60638804
Application Number:	60651128
Application Number:	60639442
Application Number:	11314032
Application Number:	60717164
Application Number:	60717163
Application Number:	11317339

CORRESPONDENCE DATA

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PATENT

REEL: 039551 FRAME: 0232

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ATTORNEY DOCKET NUMBER:	SD CORP TO SDT LLC CO-OWN
NAME OF SUBMITTER:	SIMONA BENJAMIN
SIGNATURE:	/SB/
DATE SIGNED:	08/03/2016
Total Attachments: 9	
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ASSIGNMENT

WHEREAS, SanDisk Corporation, a corporation doing business at 951 SanDisk Drive, Milpitas, CA 95035 (hereinafter referred to as Assignor), is a co-owner of all patents and patent applications listed on Schedule A together with all divisions, continuations, or continuations-in-part thereof, and all patents issuing thereon including reissues, renewals, substitutions, re-examinations and extensions thereof, and any and all corresponding foreign patents and patent applications (hereinafter referred to as, collectively, THE ASSIGNED PATENT RIGHTS);

WHEREAS, SanDisk Technologies LLC, a Texas company, doing business at 6900 Dallas Parkway, Suite 325, Plano, Texas 75024, (hereinafter referred to as Assignee), is desirous of acquiring Assignor's right, title and interest in THE ASSIGNED PATENT RIGHTS;

NOW, THEREFORE, for good and valuable consideration, the receipt of which is hereby acknowledged, Assignor hereby assigns, transfers and conveys unto the said Assignee, and Assignee accepts, all of Assignor's right, title and interest throughout the world in and to THE ASSIGNED PATENT RIGHTS and to all Letters Patent or applications or similar legal protection, not only in the United States and its territorial possessions, but in all countries foreign thereto to be obtained for THE ASSIGNED PATENT RIGHTS, and to any continuation, division, renewal, substitute or reissue thereof or any legal equivalent thereof in the United States or a foreign country for the full term or terms for which the same may be granted, including all priority rights under the International Convention; and Assignor hereby authorizes and requests the United States Commissioner of Patents and Trademarks and any officials of foreign countries whose duty it is to issue patents on applications as aforesaid, to issue all patents for THE ASSIGNED PATENT RIGHTS to Assignee in accordance with the terms of this ASSIGNMENT but subject to reserved rights including but not limited to those previously retained by, granted to, or owned by, the United States government, educational institutions or both and hereby transfers and conveys all rights of action, power and benefit belonging to or accruing from THE ASSIGNED PATENT RIGHTS including the right to undertake proceedings to recover past and future damages and claim all other relief in respect of any acts of infringement thereof whether such acts shall have been committed before or after the date of this assignment.

No other rights, immunities, or licenses, including, without limitation, any rights to any intellectual property owned, controlled or licensable by Assignor are granted or assigned to Assignee under this ASSIGNMENT, either expressly or by implication, estoppels, or otherwise, other than the rights expressly recited herein.

Assignor hereby covenants that no assignment, sale, agreement or encumbrance has been or will be made or entered into which would knowingly conflict with this Agreement;

Assignor further covenants that Assignee will, upon its lawful request, reasonably be provided with all pertinent facts and documents relating to THE ASSIGNED PATENT RIGHTS and legal equivalents as may be known and reasonably accessible to Assignor and that Assignor will testify as to the same in any administrative contest or litigation related thereto and will promptly execute and deliver to Assignee or its legal representative any and all papers, instruments or affidavits required to apply for, obtain, maintain, issue and enforce THE ASSIGNED PATENT RIGHTS and said equivalents

in the United States or in any foreign country, which may be necessary or desirable to carry out the purposes thereof.
IN TESTIMONY WHEREOF, I hereunto set my hand as of the date indicated below:

July 12, 2016 Date	Name: Michael Ray Title: President & Secretary
IN TESTIMONY WHEREOF, date indicated below:	, in accepting said Assignment, I hereunto set my hand as of th
	SANDISK TECHNOLOGIES LLC
Date ×	Name: E. Earle Thompson Title: Manager

in the United States or in any foreign country, which may be necessary or desirable to carry out the purposes thereof.

IN TESTIMONY WHEREOF, I hereunto set my hand as of the date indicated below:

	SANDISK CORPORATION	
Date	Name:	
	Title:	

IN TESTIMONY WHEREOF, in accepting said Assignment, I hereunto set my hand as of the date indicated below:

July 12, 2016

SANDISK TECHNOLOGIES LLC

Name: E. Earle Thompson

Title: Manager

585 *	11-20	Country		Application #	Date Filed	Patent #	Grant Date	Status
FLV0001.000CN	Operating Techniques For Reducing Effects Of Coupling Between Storage Elements Of A Non-Volatile Memory Operated in Multiple	3	Utility - NSPCT 02143467.0	02143467.0	Jun 27, 2002	ZL02143467.0	Jul 6, 2007	Issued
FLV0001.001CN	Operating Techniques For Reducing Effects Of Coupling Between Storage Elements Of A Non-Volatile Memory Operated in Multiple	Ç.	Utility - DIV	200710153755.5	Jun 27, 2002	ZI.200710153755.5	Feb 8, 2012	Issued
FLV0002.000CN	Non-Volatic Semiconductor Memory With Large Erase Blocks	Ş	Utility - ORG	200380109217.6	Dec 18, 2003	ZL200380109217.6	Oct 6, 2010	issued
FLV0003.000CN	Non-Volatel Esemiconductor Memory Device Adapted to Store a Munti-Valuate Data in a Storia Memory Cell Multi-Valuate Data in a Storia Memory Cell	CN	Utility - ORG	02106452.0	Feb 28, 2002	ZL02106452.0	Sep 19, 2007	issued
FLV0003.00ZCN	Non-Valuelle Semiconductor Memory Device Adapted to Store a Multi-Valuelle Data in a Single Memory Cell	S	Utility - DIV	200510116413.7	Feb 28, 2002	ZL200510116413.7	Sep 9, 2009	Issued
FLV0004.000CN	Methods For Identifying Non-Volatile Memory Elements With Proc Subthershold Slace Or Weak Transconductains	S	Utility - NSPCT	200480026763.8	Sep 16, 2004	ZL200480026763.8	Oct 12, 2011	Issued
FLV0004.001CN	Methods for Identifying Non-Volatile Memory Elements With	S	Utility - DIV	201110204417.6	Sep 16, 2004	ZL201110204417.6	Jul 16, 2014	issued
FLV0005.000CN	Behavior Based Programming of Non-Volatile Memory	2	Utility - ORG	200410032925.0	Apr 16, 2004	ZL200410032925.0	Aug 19, 2009	issued
FLV0006.000CN	Non-Volatile Semiconductor Memory Device Which Uses Some Memory Blocks in Multilevel Memory as Binary Memory Blocks	Q	Utility - NSPCT	Utility - NSPCT 200480027371.3	Aug 23, 2004	ZL200480027371.3	Oct 6, 2010	Issued
FLV0007.000CN	Non-Volatile Semiconductor Memory Device Having Protection Function for Each Memory Block	CN	Utility - NSPCT	Utility - NSPCT 200480027761.0	Aug 23, 2004	ZL200480027761.0	Sep 22, 2010	Issued
FLV0008.000CN	Behavior Based Programming of Non-Volatile Memory	S	Utility - NSPCT	Utility - NSPCT 200480030734.9	Oct 12, 2004	ZL200480030734.9	Apr 14, 2010	Issued
SDK0572.000CN	Secure Memory Card With Life Cycle Phases	3	Utility - NSPCT	Utility - NSPCT 200680004229.6	Feb 1, 2006	ZL200680004229.6	Jun 16, 2010	Issued
SDK0733.000CN	Secure yet flexible system architecture for secure devices with flash mass storage memory	2	Utility - NSPCT	Utility - NSPCT 200680033896.7	Sep 13, 2006	ZL200680033896.7	Jul 17, 2013	lssued
FLV0001.000DE	Operating Techniques For Reducing Effects Of Coupling Between Storage Elements Of A Non-Volatile Memory Operated in Multiple Data States	DE	Utility - EPPAT	02254491.0	Jun 26, 2002	1271553	Jun 13, 2007	Issued
FLV0001.001DE	Operating Techniques For Reducing Effects Of Coupling Between Storage Elements Of A Non-Volatile Memory Operated in Multiple Data States	30	Utility - EPPAT 070063441	070063441	Jun 26, 2002	1814122	May 15, 2013	Ssued
FLV0002.000DE	Non-Volation Non-V	æ	Utility - EPPAT	03815779.8	Dec 18, 2003	1588379	Feb 27, 2008	Issued
FLV0002.001DE	Non-Volatile Semiconductor Memory With Large Erase Blocks Storing Cycle Counts	DE.	Utility - EPPAT	070760277	Dec 18, 2003	1975942	Jun 6, 2012	Issued
FLV0003.000DE	Non-Volatile Semiconductor Memory Device Adapted to Store a Multi-Valued Data in a Single Memory Cell	DE	Utility - EPPAT	02001104.5	Jan 23, 2002	1324343	May 7, 2014	Issued
FLV0004.000DE	Methods For identifying Non-Volatile Memory Elements With Poor Subthreshold Slove Or Weak Transconductance	DE.	Utility - EPPAT	04784376.8	Sep 16, 2004	1665285	Apr 23, 2008	Issued
FLV0004.001DE	Methods For identifying Non-Volatile Memory Elements With Door Schibbreshold Sinne Or West Transconductors	В	Utility - EPPAT 080043458	080043458	Sep 16, 2004	2015310	Nov 9, 2011	Issued
FLV0005.000DE	Behavior Based Programming of Non-Volatile Memory	30	Utility - EPPAT	04008974.0	Apr 15, 2003	1469480	Aug 5, 2009	Issued
FLV0008.000DE	BEHAVIOR BASED PROGRAMMING OF NON-VOLATHE MEMORY [FLV0008 000FP] [formerly 5DX0468.000US]	DE	Utility - EPPAT	04795181.9	Oct 12, 2004	1678722	Jan 19, 2011	Issued

**	Title	Country	ədáş səştepy	Application #	Date Filed	Patent #	Grant Date	Status
FLV0006.000EP	Volatile Semiconductor Memory Device Which Uses Some nory Blocks in Multilevel Memory as Binary Memory Blocks	ΕĢ	-41	04772376.2	Aug 23, 2004			Published
FLV0007.000EP	mory Device Having Protection	Ę	Utility - NSPCT 04772375.4	04772375.4	Aug 23, 2004			Published
FI.V0001.001FR	chniques for Reducing Effects Of Coupling Between chniques for Reducing Effects Of Coupling Between the control of A Non-Volatile Memory Operated in Multiple	77.72	Utility - EPPAT	070063441	Jun 26, 2002	1814122	May 15, 2013	lssued
FLV0002.000FR	Non-Volatile Semiconductor Memory With Large Erase Blocks Stocing Cycle Counts	FR	Utility - EPPAT	03815779.8	Dec 18, 2003	1588379	Feb 27, 2008	issued
FLV0002.001FR	nductor Memory With Large Erase Blocks	Æ	Utility - EPPAT 070760277	070760277	Dec 18, 2003	1975942	Jun 6, 2012	Issued
FLV0004.000FR	nts With	FR	Utility - EPPAT 04784376.8	04784376.8	Sep 16, 2004	1665285	Apr 23, 2008	Issued
FLV0004.001FR	Methods For Identifying Non-Volatile Memory Elements With Prof Suithbreshold Sinns Or Weak Transconductance	FR	Utility - EPPAT 080043458	080043458	Sep 16, 2004	2015310	Nov 9, 2011	Issued
FLV0005.000FR	Y	FR	Utility - EPPAT 04008974.0	04008974.0	Apr 15, 2003	1469480	Aug 5, 2009	issued
FLV0008.000FR	BEHAVIOR BASED PROGRAMMING OF NON-VOLATILE MEMORY (FLYCKOR COCEP) (formerly SDK0468, 000US)	FR	Utility - EPPAT	04795181.9	Oct 12, 2004	1678722	Jan 19, 2011	issued
FLV0001.000GB	· 0	980	Utility - EPPAT	02254491.0	Jun 26, 2002	1271553	Jun 13, 2007	issued
FLV0001.001G8	echniques For Reducing Effects Of Coupling Between ments Of A Non-Volatile Memory Operated in Multiple	GB	Utility - EPPAT 070063441	070063441	Jun 26, 2002	1814122	May 15, 2013	Issued
FLV0002.000GB	Non-Volation Non-Volation Non-Volation Storing Cycle Counts	GB	Utility - EPPAT 03815779.8	03815779.8	Dec 18, 2003	1588379	Feb 27, 2008	Issued
FLV0002.001GB	nductor Memory With Large Erase Blocks	85	Utility - EPPAT 070760277	070760277	Dec 18, 2003	1975942	Jun 6, 2012	Issued
FLV0003.000GB	nductor Memory Device Adapted to Store a a Single Memory Cell	GB	Utility - EPPAT 02001104.5	02001104.5	Jan 23, 2002	1324343	May 7, 2014	Issued
FLV0004.000GB	nory Elements With	GB	Utility - EPPAT 04784376.8	04784376.8	Sep 16, 2004	1665285	Apr 23, 2008	Issued
FLV0004.001GB	ts With	GB	Utility - EPPAT	080043458	Sep 16, 2004	2015310	Nov 9, 2011	Issued
FLV0005.000GB	~	GB GB	Utility - EPPAT	04008974.0	Apr 15, 2003	1469480	Aug 5, 2009	Issued
FLV0008.000GB	BEHAVIOR BASED PROGRAMMING OF NON-VOLATILE MEMORY IFF VIOUS CICLED (Formerly SDXDASS DOOLS)	85	Utility - EPPAT 04795181.9	04795181.9	Oct 12, 2004	1678722	Jan 19, 2011	Issued
FLV0001.000IT	of Coupling Between Operated in Multiple		Utility - EPPAT 02254491.0	02254491.0	Jun 26, 2002	1271553	Jun 13, 2007	Issued
FLV0002.000IT	e Semiconductor Memory With Large Erase Blocks e Counts	Ŧ	Utility - EPPAT 03815779.8	03815779.8	Dec 18, 2003	1588379	Feb 27, 2008	Issued
FLV0004.000IT	ing Non-Volatile Memory Elements With ope Or Weak Transconductance	7	Utility - EPPAT 04784376.8	04784376.8	Sep 16, 2004	1665285	Apr 23, 2008	Issued
ELV0001.000JP	ւք Between d In Multiple	JP qf	Utilky - NSPCT 2002-187020	2002-187020	Jun 27, 2002	4221196	Nov 21, 2008	Issued

File#	Tele	Country	Matter type	Application #	Date Filed	Patent #	Grant Date	Status
FLV0002.000JP	Volatile Semiconductor Memory With Large Erase Blocks	JP G		2004-568035	Dec 18, 2003	4648006	Dec 17, 2010	Issued
FLV0003.000JP	nductor Memory Device Adapted to Store a	d d	Utility - ORG	2001-397446	Dec 27, 2001	3631463	Dec 24, 2004	Issued
FLV0004.000JP	nts With	Ė	Utility - NSPCT 2004-304919	2004-304919	Sep 17, 2004	5198717	Feb 15, 2013	Issued
FLV0005.000JP	Behavior Based Programming of Non-Volatile Memory	Jp	Utility - ORG	2003-114762	Apr 18, 2003	4314057	May 22, 2009	Issued
FLV0006.000JP	Non-Volatile Semiconductor Memory Device Which Uses Some Memory Blocks in Multilevel Memory as Binary Memory Blocks	ë	Utility - ORG	2009-338545	Sep 29, 2003	4270994	Mar 6, 2009	Issued
FLV0008.000JP	BEHAVIOR BASED PROGRAMMING OF NON-VOLATILE MEMORY	*	Utility - NSPCT 2004-76471	2004-76471	Mar 17, 2004	4646534	Dec 17, 2010	Issued
FLV0011.000JP	FABRICATION OF SEMICONDUCTOR DEVICE FOR FLASH MEMORY WITH INCREASED SELECT GATE WIDTH (FLV0011.000US)	ਰ	Utility - NSPCT 2008-548758	2008-548758	Dec 27, 2006	4934149	Feb 24, 2012	Issued
FLV0013.000JP	Nonvolatile semiconductor memory device and manufacturing method thereof	ξ	Utility - ORG	2008-254988	Sep 30, 2008	5548350	Мау 23, 2014	Issued
F1V0015.001JP	ge Memory	de de	Utility - ORG	2013-182442	Sep 17, 2013			Pending
SDK0571.000-I-JP	Memory System with Versatile Content Control	de .	Utility - DIV	2010-049119	Dec 21, 2005	4848039	Oct 21, 2011	Issued
SDK0571.000JP	Memory System With Versatile Content Control	- Light	Utility - NSPCT 2007-548449	2007-548449	Dec 21, 2005	4847967	Oct 21, 2011	Issued
SDK0572.000JP	Secure Memory Card With Life Cycle Phases	Ā	Utility - NSPCT 2007-554249	2007-554249	Feb 1, 2006	4787273	Jul 22, 2011	Issued
SDK0726.000JP	Memory System With in Stream Data Encryption / Decryption	9	Utility - NSPCT 2007-548469	2007-548469	Dec 21, 2005	5118494	Oct 26, 2012	issued
SDK0733.000JP	Secure yet flexible system architecture for secure devices with flash mass storage memory	JP	Utility - NSPCT	2008-531323	Sep 13, 2006	4891324	Dec 22, 2011	Issued
FLV0001.000XR	educing Effects Of Coupling Between Volatile Memory Operated in Multiple	XX	Utility - NSPCT 2002-36424	2002-36424	Jun 27, 2002	10-0926950	Nov 9, 2009	Issued
FLV0002.000KR	s Semiconductor Memory With Large Erase Blocks e Counts	Ş	Utility - NSPCT	Utility - NSPCT 2005-7013970	Dec 18, 2003	10-1089575	Nov 29, 2011	Issued
FLV0003.000KR	iductor Memory Device Adapted to Store a a Single Memory Cell	X 22	Utility - ORG	2002-0010414	Jul 8, 2004	467410	Jan 12, 2005	issued
FLV0004.000KR	Methods For Identifying Non-Volatile Memory Elements With Poor Subthreshold Slope Or Weak Transconductance	X 20	Utility - NSPCT	Utility - NSPCT 2006-7005470	Sep 16, 2004	19-1124175	Feb 29, 2012	Issued
FLV0005,000KR	Behavior Based Programming of Non-Volatile Memory	æ	Utility - ORG	2004-24773	Apr 14, 2004	599905	Jul 5, 2006	Issued
FLV0005.000KR	Non-Volatile Semiconductor Memory Device Which Uses Some Memory Blocks in Multilevel Memory as Binary Memory Blocks	K	Utility - NSPCT	Utility - NSPCT 2006-7005576	Aug 23, 2004	10-721062	May 16, 2007	issued
FLV0007.000KR	Non-Volatile Semiconductor Memory Device Having Protection Function for Each Memory Block	X 33	Utility - NSPCT	Utility - NSPCT 2006-7005766	Aug 23, 2004	10-721061	May 16, 2007	issued
FLV0008.000KR	BEHAVIOR BASED PROGRAMMING OF NON-VOLATILE MEMORY	X 22	Utility - NSPCT	2006-7007560	Oct 12, 2004	10-1161429	Jun 25, 2012	Issued
FLV0008.001KR	BEHAVIOR BASED PROGRAMMING OF NON-VOLATILE MEMORY	X	Utility - DIV	2012-7009782	Oct 12, 2004	10-1323843	Oct 24, 2013	issued

File #	Title	Country	Matter type	Application #	Date Filed	Patent #	Grant Date	Status
SDK0571.000-I-KR	nory System With Versatile Content Control	KR	Utility - DIV	2009-7026878	Dec 21, 2005	10-1213118	Dec 11, 2012	issued
SDK0571.000KR	Memory System With Versatile Content Control	KR	Utility - NSPCT 2007-7016643	2007-7016643	Dec 21, 2005	10-1214497	Dec 14, 2012	Issued
SDK0572,000KR	Secure Memory Card With Life Cycle Phases	S	Utility - NSPCT 2007-7018143	2007-7018143	Feb 1, 2006	10-0972540	Jul 21, 2010	Issued
SDK0726.000KR	Memory System With In Stream Data Encryption / Decryption	XX.	Utility - NSPCT	Utility - NSPCT 2007-7016700	Dec 21, 2005	10-1297760	Aug 12, 2013	Issued
SDK0726.001KR	Memory System With In Stream Data Encryption / Decryption	KR	Utility - DIV	2012-7027415	Dec 21, 2005	10-1323746	Oct 22, 2013	Issued
SDK0733.000KR	Secure yet fiexible system architecture for secure devices with flash mass storage memory	X,	Utility - NSPCT 2008-7006257	2008-7006257	Sep 13, 2006	10-1014179	Feb 7, 2011	Issued
FLV0001.000NL	educing Effects Of Coupling Between Volatile Memory Operated in Multiple	Z	Utility - EPPAT 02254491.0	02254491.0	Jun 26, 2002	1271553	Jun 13, 2007	Issued
FLV0001.001NL	Operating Techniques For Reducing Effects Of Coupling Between Storage Elements Of A Non-Volatile Memory Operated in Multiple Data States	2	Utility - EPPAT 070063441	070063441	Jun 26, 2002	1814122	May 15, 2013	issued
FLV0002.000NL	≥ Semiconductor Memory With Large Erase Blocks e Counts	ž	Utility - EPPAT 03815779.8	03815779.8	Dec 18, 2003	1588379	Feb 27, 2008	Issued
FLV0002.001NL	nductor Memory With Large Erase Blocks	N.	Utility - EPPAT 070760277	070760277	Dec 18, 2003	1975942	Jun 6, 2012	Issued
FLV0004.000NL	ing Non-Volatile Memory Elements With one Or Weak Transconductance	Z.	Utility - EPPAT 04784376.8	04784376.8	Sep 16, 2004	1665285	Apr 23, 2008	Issued
FLV0004.001NL	nts With	718	Utility - EPPAY 080043458	080043458	Sep 16, 2004	2015310	Nov 9, 2011	issued
FLVOOO8.000NL	E MEMORY	N.	Utility - EPPAT	04795181.9	Oct 12, 2004	1678722	Jan 19, 2011	Issued
FLV0001.000TW	if Coupling Between Operated in Multiple	W	Utility - ORG	091113894	Jun 25, 2002	1199878	Aug 3, 2004	Issued
FLV0002,000TW	Non-Volatile Semiconductor Memory With Large Erase Blocks Storing Cycle Counts	WI	Utility - ORG	93101054	Jan 15, 2004	1323466	Apr 11, 2010	Issued
FLV0003.000TW	Non-Volatile Semiconductor Memory Device Adapted to Store a Milfs-Valued Data in a Single Memory Cell	WT	Utility - ORG	091103610	Feb 27, 2002	182686	Nov 24, 2003	Issued
FLV0004.000TW	Methods For Identifying Non-Volatile Memory Elements With Poor Subthreshold Slope Or Weak Transconductance	¥ï	Utility - ORG	093128293	Sep 17, 2004	1264009	Oct 11, 2006	Issued
FLV0005.000TW	Behavior Based Programming of Non-Volatile Memory	WI	Utility - ORG	093110558	Apr 15, 2004	1237270	Aug 1, 2005	Issued
FLV0006.000TW	Non-Volatile Semiconductor Memory Device Which Uses Some Memory Blocks in Multilevel Memory as Binary Memory Blocks	TW	Utility - ORG	93125649	Aug 26, 2004	1251833	Mar 21, 2006	Issued
FLV0007.000TW	Non-Volatile Semiconductor Memory Device Having Protection Function for Each Memory Block	.TW	Utility - ORG	93125655	Aug 26, 2004	1266326	Nov 11, 2006	Issued
FLVOQO8.000TW	Behavior Based Programming of Non-Volatile Memory	WT	Utility - ORG	093131854	Oct 20, 2004	1262506	Sep 21, 2006	Issued
M100011'0001M	FABRICATION OF SEMICONDUCTOR DEVICE FOR FLASH MEMORY WITH INCREASED SELECT GATE WIDTH (FLV0011.000US)	WT	Utility - ORG	095149282	Dec 27, 2006	1333263	Nov 11, 2010	Issued

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FLV0001.000US	Operating Techniques For Reducing Effects Of Coupling Between	US	Utility - ORG	09/893,277	Jun 27, 2001	6,522,580	Feb 18, 2003	Issued
	10			· ·				
F1.V0001.001US	NonVolatile Memory Capable of Reducing Effects of	SS	Utility - CON	10/323,534	Dec 18, 2002	6,807,095	Oct 19, 2004	Issued
FLV0001.002US	echniques for Reducing Effects of Coupling Between ments of a Non-Volatile Memory Operated in Multiple	S	Utility - CON	10/966,451	Oct 15, 2004	7,061,798	Jun 13, 2006	Issued
FLV0001.003US	echniques for Reducing Effects of Coupling Between nents of a Non-Volatile Memory Operated in Multiple	S	Utility - DIV	11/205,595	Aug 16, 2005	7,224,613	May 29, 2007	issued
FLV0002.000US	Non-Volation Non-Volation Storing Cycle Counts	rs.	Utility - ORG	10/353,574	Jan 28, 2003	6,944,063	Sep 13, 2005	Issued
FLV0002.001US	nductor Memory With Large Erase Blocks	Sn	Utility - DIV	11/004,139	Dec 2, 2004	7,307,881	Dec 11, 2007	Issued
FLV0002.00ZUS	iductor Memory With Large Erase Blocks	US	Utility - DIV	11/003,046	Dec 2, 2004	7,085,161	Aug 1, 2006	issued
FLV0002.003US	nductor Memory With Large Erase Blocks	Sn	Utility - CON	11/419,696	May 22, 2006	7,394,692	Jul 1, 2008	Issued
FLV0003.000US	nductor Memory Device Adapted to Store a a Single Memory Cell	US	Utility - ORG	10/051,372	Jan 22, 2002	6,643,188	Nov 4, 2003	Issued
FLV0003.001US	ed To Store A Multi-	US	Utility - DIV	10/656,139	Sep 8, 2003	6,990,019	Jan 24, 2006	issued
FLV0003.002US	Adapted To Store A Multi-	US	Utility - DIV	11/049,535	Feb 3, 2005	7,088,616	Aug 8, 2006	issued
FLV0003.003US	/ Device Adapted to Store a v Cell	รถ	Utility - CON	11/417,185	May 4, 2006	7,286,404	Oct 23, 2007	Issued
FLV0003.004US	ce Adapted to Store a	Sn	NOO - AIIIIAN	11/871,441	Oct 12, 2007	7,405,970	Jul 29, 2008	Issued
FLV0003.005U\$	ice Adapted to Store a	US	Utility - CON	12/168,283	Jul 7, 2008	7,672,168	Mar 2, 2010	issued
FLV0003.006US	ce Adapted to Store a	US	Utility - CON	12/652,418	Jan 5, 2010	7,864,591		issued
FLV0003.007US	ce Adapted to Store a	เร	Otility - CON	12/967,227	Dec 14, 2010	8,208,311	Jun 26, 2012	issued
FLV0003.008US	ce Adapted to Store a	US	Utility - CON	13/482,577	Мау 29, 2012	8,605,511	Dec 10, 2013	ssued
FLV0003.009US	ce Adapted to Store a	US	Utility - CON	14/078,195	Nov 12, 2013	8,929,135	Jan 6, 2015	ssued
FLV0003.010US	ce Adapted to Store a	US	Utility - CON	14/559,265	Dec 3, 2014	9,257,189	Feb 9, 2016	{ssued
FLV0003.011US	ce Adapted to Store a	Sn	Utility - CON	14/983,802	Dec 30, 2015			Pending
FLV0004.000US	nts With	Sn	Utility - ORG	10/665,685	Sep 17, 2003	7,046,555	May 16, 2006	issued
FLV0004.001US	Methods for identifying non-volatile memory elements with poor subthreshold slope or weak transconductance	Sn	Utility - DIV	11/389,557	Mar 23, 2006	7,414,894	Aug 19, 2008	Issued
FLV0005.000US	Sectronic Card	US	Utility - ORG	10/823,737	Apr 14, 2004	6,990,018	Jan 24, 2006	Issued
FLV0005.001US	vice, Electronic Card	US	Utility - CON	11/289,509	Nov 30, 2005	7,394,704	Jul 1, 2008	Issued
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FLV0006.000US	Non-Volatile Semiconductor Memory Device Which Uses Some Memory Blocks in Multilevel Memory as Binary Memory Blocks	us		11/391,299	Mar 29, 2006			Abandoned
FLV0007.000US	Non-Volatile Semiconductor Memory Device Having Protection	S	Utility - NSPCT	11/387,818	Aug 23, 2004	7,376,010	May 20, 2008	Issued
FLV0007.001US	Non-Volatile Semiconductor Memory Device Having Protection	SO	Utility - DIV	12/108,272	Apr 23, 2008	7,787,296	Aug 31, 2010	Issued
FLV0007.002US	Non-Volatile Semiconductor Memory Device Having Protection Function for Earth Memory Block	S	Utility - DIV	12/846,118	Jul 29, 2010	7,952,925	May 31, 2011	Issued
FLV0007.003US	Non-Volatile Semiconductor Memory Device Having Protection	US	Utility - DIV	13/099,024	May 2, 2011	8,111,551	Feb 7, 2012	Issued
FLV0008.000US	Behavior Based Programming on Non-Volatile Memories	Sn	Utility - ORG	10/689,333	Oct 20, 2003	7,177,199	Feb 13, 2007	Issued
FLV0008.001US	BEHAVIOR BASED PROGRAMMING OF NON-VOLATILE MEMORY	us	Utility - CON	11/624,052	Jan 17, 2007	7,633,807	Dec 15, 2009	issued
FLV0009.000US	A 146mm2 85b NAND Flash Memory with 70nm CMOS	Sn	Prov - ORG	60/612,089	Sep 21, 2004			Abandoned
FLV0011.000US	FABRICATION OF SEMICONDUCTOR DEVICE FOR FLASH MEMORY WITH INCREASED SELECT GATE WIDTH	US.	Utility - ORG	11/319,895	Dec 28, 2005	7,365,018	Apr 29, 2008	issued
FLV0015.000US	Resistance Change Memory	S	Prov - ORG	61/822,009	Jun 10, 2013			Completed
FLV0015.001US	Resistance Change Memory	SO	Utility -	14/018,790	Sep 5, 2013	9,117,516	Aug 25, 2015	Issued
FLV0016.000US	Semiconductor Device	IJ	Utility - ORG	14/200,819	Mar 7, 2014			Abandoned
FLV0016.001US	Semiconductor Device	S	Utility - CIP	14/638,817	Mar 4, 2015			Published
FLV0017.000US	Temperature Sensor	Sn	Prov - ORG	61/876,539	Sep 11, 2013			Completed
FLV0017.001US	Temperature Sensor	SO	Otility -	14/199,082	Mar 6, 2014			Pending
FLV0343.000PP	125mm2 1Gb NAND Flash Memory With 10 MB/s Program Throughout	us	ž	60/356,455	Feb 11, 2002			Completed
SDK0022.003US	Wear Leveling Techniques for Flash EEPROM Systems	SS	Utility - ORG	09/838,817	Apr 19, 2001			Abandoned
SDK0022.006US	Wear Leveling Techniques for Flash EEPROM Systems	SS	Utility - DIV	12/038,666	Feb 27, 2008			Abandoned
SDK0571.000US	Memory System With Versatile Content Control	S	Prov - ORG	60/638,804	Dec 21, 2004			Completed
SDK0572.000US	Secure Memory Card With Life Cycle Phases	S	Prov - ORG	60/651,128	Feb 7, 2005			Completed
SDK0726.000US	Memory System With In-Stream Data Encryption/Decryption	S	Prov - ORG	60/639,442	Dec 21, 2004			Completed
SDK0726.002US	Memory system with an in stream data encryption/decryption	S	Utility -	11/314,032	Dec 20, 2005			Abandoned
SDK0733.000US	Secure Yet Flexible System Architecture for Secure Devices With Flash Mass Storage Memory	S	Prov - ORG	60/717,164	Sep 14, 2005			Completed
SDK0733.001US	Secure Yet Flexible System Architecture for Secure Devices With Flash Mass Storage Memory	S	Prov - ORG	60/717,163	Sep 14, 2005			Completed
SDK0733.003US	Secure Yet Flexible System Architecture for Secure Devices With Fiash Mass Storage Memory	ß	Utility - ORG	11/317,339	Dec 22, 2005			Abandoned

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